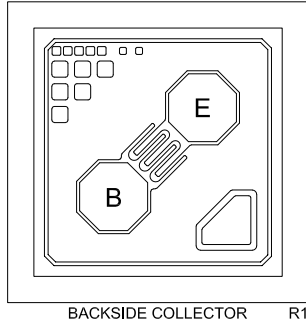


The CP617-CM4957 is a silicon PNP RF transistor designed for high frequency amplifier and non-saturated switching applications.



**MECHANICAL SPECIFICATIONS:**

Die Size	15.7 x 15.7 MILS
Die Thickness	7.9 MILS
Base Bonding Pad Size	3.54 x 3.54 MILS
Emitter Bonding Pad Size	3.54 x 3.54 MILS
Top Side Metalization	Al – 9,000Å
Back Side Metalization	Au – 10,000Å
Scribe Alley Width	2.9 MILS
Wafer Diameter	4 INCHES
Gross Die Per Wafer	44,140

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

	SYMBOL		UNITS
Collector-Base Voltage	$V_{CBO}$	30	V
Collector-Emitter Voltage	$V_{CEO}$	25	V
Emitter-Base Voltage	$V_{EBO}$	3.0	V
Continuous Collector Current	$I_C$	30	mA
Continuous Base Current	$I_B$	2.0	A
Operating and Storage Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$

**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$I_{CBO}$	$V_{CB}=10\text{V}$			100	nA
$BV_{CBO}$	$I_C=100\mu\text{A}$	30			V
$BV_{CEO}$	$I_C=1.0\text{mA}$	25			V
$BV_{EBO}$	$I_E=100\mu\text{A}$	3.0			V
$h_{FE}$	$V_{CE}=10\text{V}, I_C=2.0\text{mA}$	20		150	
$h_{fe}$	$V_{CE}=10\text{V}, I_C=2.0\text{mA}, f=1.0\text{kHz}$	20		200	
$C_{cb}$	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$		1.6	2.0	pF
$f_T$	$V_{CE}=10\text{V}, I_C=2.0\text{mA}, f=100\text{MHz}$	1200		2500	MHz
$G_{pe}$	$V_{CE}=10\text{V}, I_C=4.0\text{mA}, f=450\text{MHz}$	17		25	dB

# CP617-CM4957

## Typical Electrical Characteristics

